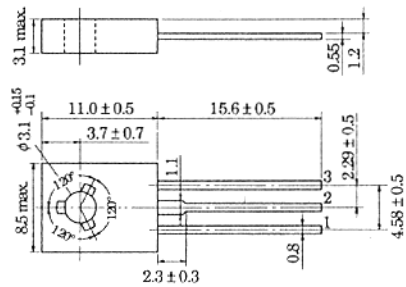


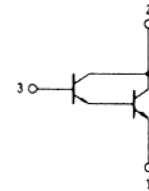
2SC2298

SILICON NPN EPITAXIAL HIGH GAIN AMPLIFIER



1. Emitter
2. Collector
3. Base

(Dimensions in mm)



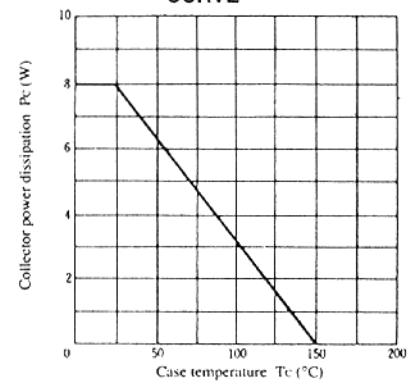
(JEDEC TO-126 MOD.)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC2298	Unit
Collector to base voltage	V _{CBO}	30	V
Collector to emitter voltage	V _{CEO}	30	V
Emitter to base voltage	V _{EB0}	10	V
Collector current	I _C	1.0	A
Collector peak current	i _{C(peak)}	1.5	A
Collector power dissipation	P _C	0.8	W
	P _C *	8	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Value at $T_c = 25^\circ\text{C}$

MAXIMUM COLLECTOR DISSIPATION
CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	30	—	—	V
Emitter cutoff current	I_{EBO}	$V_{EB} = 10\text{V}, I_C = 0$	—	—	10	μA
DC current transfer ratio	h_{FE1}^*	$V_{CE} = 3\text{V}, I_C = 10\text{mA}$	4000	—	—	
	h_{FE2}^*	$V_{CE} = 3\text{V}, I_C = 100\text{mA}$	10000	—	—	
	h_{FE3}^*	$V_{CE} = 3\text{V}, I_C = 400\text{mA}$ (pulse test)	10000	—	—	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 400\text{mA}, I_B = 0.1\text{mA}$ (pulse test)	—	—	1.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$		—	—	2.0	V

* The 2SC2298 is grouped by hFE as follows.

